

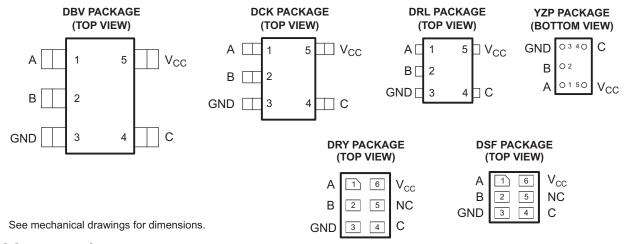
SINGLE BILATERAL ANALOG SWITCH

Check for Samples: SN74LVC1G66

FEATURES

- Available in the Texas Instruments NanoFree™ Package
- 1.65-V to 5.5-V V_{CC} Operation
- Inputs Accept Voltages to 5.5 V
- Max t_{pd} of 0.8 ns at 3.3 V
- · High On-Off Output Voltage Ratio
- High Degree of Linearity
- High Speed, Typically 0.5 ns (V_{CC} = 3 V, C_L = 50 pF)

- Low On-State Resistance, Typically ≉5.5 Ω (V_{CC} = 4.5 V)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)



DESCRIPTION/ORDERING INFORMATION

This single analog switch is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G66 can handle both analog and digital signals. The device permits signals with amplitudes of up to 5.5 V (peak) to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



Table 1. ORDERING INFORMATION

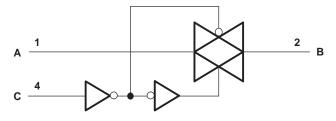
T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽²⁾	
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74LVC1G66YZPR	C6_	
	SOT (SOT-23) – DBV	Reel of 3000	SN74LVC1G66DBVR	Cee	
		Reel of 250	SN74LVC1G66DBVT	C66_	
–40°C to 85°C	SOT (SC-70) – DCK	Reel of 3000	SN74LVC1G66DCKR		
		Reel of 250	SN74LVC1G66DCKT	C6_	
	SOT (SOT-553) – DRL	Reel of 4000	SN74LVC1G66DRLR		
	QFN – DRY Reel of		SN74LVC1G66DRYR	- C6	
	μQFN – DSF	Reel of 5000	SN74LVC1G66DSFR	Co	

- (1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
- (2) DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site. YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, = Pb-free).

FUNCTION TABLE

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON

LOGIC DIAGRAM (POSITIVE LOGIC)



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Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range ⁽²⁾		-0.5	6.5	V
V_{I}	Input voltage range (2) (3)		-0.5	6.5	٧
V _{I/O}	Switch I/O voltage range ^{(2) (3) (4)}		-0.5	V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V ₁ < 0		-50	mA
I_{IOK}	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		±50	mA
I _T	On-state switch current	$V_{I/O}$ < 0 to V_{CC}		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
		DBV package		206	
0	Package thermal impedance (5)	DCK package		252	°C/W
θ_{JA}	Package thermal impedance **	DRL package		142	C/VV
		YZP package		132	
T _{stg}	Storage temperature range	·	-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

Product Folder Link(s): SN74LVC1G66

²⁾ All voltages are with respect to ground, unless otherwise specified.

⁽³⁾ The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁴⁾ This value is limited to 5.5 V maximum.

⁽⁵⁾ The package thermal impedance is calculated in accordance with JESD 51-7.



Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		1.65	5.5	V
V _{I/O}	I/O port voltage		0	V_{CC}	V
		V _{CC} = 1.65 V to 1.95 V	V _{CC} × 0.65		
\ /	Lligh level input valtage, control input	V_{CC} = 2.3 V to 2.7 V	V _{CC} × 0.7		V
V _{IH}	High-level input voltage, control input	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	V _{CC} × 0.7		V
		V _{CC} = 4.5 V to 5.5 V	V _{CC} × 0.7		
		V _{CC} = 1.65 V to 1.95 V		V _{CC} × 0.35	
.,	A service of the service to the serv	V _{CC} = 2.3 V to 2.7 V		V _{CC} × 0.3	V
V _{IL}	Low-level input voltage, control input	V _{CC} = 3 V to 3.6 V		V _{CC} × 0.3	V
		V _{CC} = 4.5 V to 5.5 V		$V_{CC} \times 0.3$	
VI	Control input voltage		0	5.5	V
		V _{CC} = 1.65 V to 1.95 V		20	
۸ + / ۸	land the political vise (fall times	V _{CC} = 2.3 V to 2.7 V		20	0/
Δt/Δv	Input transition rise/fall time	V _{CC} = 3 V to 3.6 V		10	ns/V
		V _{CC} = 4.5 V to 5.5 V		10	
T _A	Operating free-air temperature		-40	85	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CO	NDITIONS	V _{CC}	MIN TYP ⁽¹⁾	MAX	UNIT
		$V_I = V_{CC}$ or GND,	$I_S = 4 \text{ mA}$	1.65 V	12	30	
_	On-state switch resistance	$V_C = V_{IH}$	$I_S = 8 \text{ mA}$	2.3 V	9	20	Ω
r _{on}	On-state switch resistance	(see Figure 1 and Figure 2)	$I_S = 24 \text{ mA}$	3 V	7.5	15	22
		Figure 2)	$I_S = 32 \text{ mA}$	4.5 V	5.5	10	
		$V_I = V_{CC}$ or GND,	$I_S = 4 \text{ mA}$	1.65 V	74.5	120	
_	Peak on resistance	$V_C = V_{IH}$	$I_S = 8 \text{ mA}$	2.3 V	20	30	Ω
r _{on(p)}	Peak on resistance	(see Figure 1 and	$I_S = 24 \text{ mA}$	3 V	11.5	20	12
		Figure 2)	I _S = 32 mA	4.5 V	7.5	15	
	Off-state switch leakage	$V_I = V_{CC}$ and $V_O = GN$	D or			±1	
I _{S(off)}	current	$V_I = GND$ and $V_O = V_C$ $V_C = V_{IL}$ (see Figure 3)	CC,)	5.5 V		±0.1 ⁽¹⁾	μA
	On-state switch leakage	$V_I = V_{CC}$ or GND, $V_C =$: V _{IH} , V _O = Open	5.5 V		±1	
I _{S(on)}	current	(see Figure 4)		5.5 V		±0.1 ⁽¹⁾	μA
	Control input current	$V_C = V_{CC}$ or GND		5.5 V		±1	μA
I _I	Control input current	vC = vCC or GIVD		3.5 V		±0.1 ⁽¹⁾	μΑ
	Cumply ourrant	$V_C = V_{CC}$ or GND		5.5 V		10	
I _{CC}	Supply current	AC = ACC OL GIAD		5.5 V		1 ⁽¹⁾	μA
ΔI_{CC}	Supply current change	$V_C = V_{CC} - 0.6 V$		5.5 V		500	μΑ
C _{ic}	Control input capacitance			5 V	2		pF
C _{io(off)}	Switch input/output capacitance			5 V	6		pF
C _{io(on)}	Switch input/output capacitance			5 V	13		pF

(1) $T_A = 25^{\circ}C$



Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 5)

PARAMETER	PARAMETER FROM TO (INPUT) (OUTPU		V _{CC} = ± 0.7	1.8 V I5 V	V _{CC} = ± 0.	2.5 V 2 V	V _{CC} = ± 0.		V _{CC} = ± 0.5		UNIT
	(INPUT)	(001P01)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or B	B or A		2		1.2		8.0		0.6	ns
t _{en} ⁽²⁾	С	A or B	2.5	12	1.9	6.5	1.8	5	1.5	4.2	ns
t _{dis} (3)	С	A or B	2.2	10	1.4	6.9	2	6.5	1.4	5	ns

⁽¹⁾ t_{PLH} and t_{PHL} are the same as t_{pd}. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	TYP	UNIT
				1.65 V	35	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	120	
			f _{in} = sine wave (see Figure 6)	3 V	175	
Frequency response ⁽¹⁾	A == D	D A		4.5 V	195	N 41 1-
(switch ON)	A or B	B or A		1.65 V	>300	MHz
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	>300	
			f _{in} = sine wave (see Figure 6)	3 V	>300	
				4.5 V	>300	
				1.65 V	35	
Crosstalk	0	A D	$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	50	
(control input to signal output)	С	A or B $f_{in} = 1 \text{ MHz (square wave)}$ (see Figure 7)	3 V	70	mV	
			,	4.5 V	100	
				1.65 V	-58	
		5 .	$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	2.3 V	-58	dB
			f _{in} = 1 MHz (sine wave) (see Figure 8)	3 V	-58	
Feedthrough attenuation (2)	A == D			4.5 V	-58	
(switch OFF)	A or B	B or A		1.65 V	-42	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	2.3 V	-42	
			f _{in} = 1 MHz (sine wave) (see Figure 8)	3 V	-42	
				4.5 V	-42	
				1.65 V	0.1	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025	
Cin a constant distantian			f _{in} = 1 kHz (sine wave) (see Figure 9)	3 V	0.015	%
	A or D	D ~ ^	,	4.5 V	0.01	
Sine-wave distortion	A or B	B or A		1.65 V	0.15	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	2.3 V	0.025	
			f _{in} = 10 kHz (sine wave) (see Figure 9)	3 V	0.015	
			,	4.5 V	0.01	

⁽¹⁾ Adjust f_{in} voltage to obtain 0 dBm at output. Increase f_{in} frequency until dB meter reads -3 dB.

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²⁾ t_{PZL} and t_{PZH} are the same as t_{en}.

⁽³⁾ t_{PLZ} and t_{PHZ} are the same as t_{dis}.

⁽²⁾ Adjust fin voltage to obtain 0 dBm at input.



Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT
	PARAMETER	CONDITIONS	TYP	TYP	TYP	TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	8	9	9	11	pF

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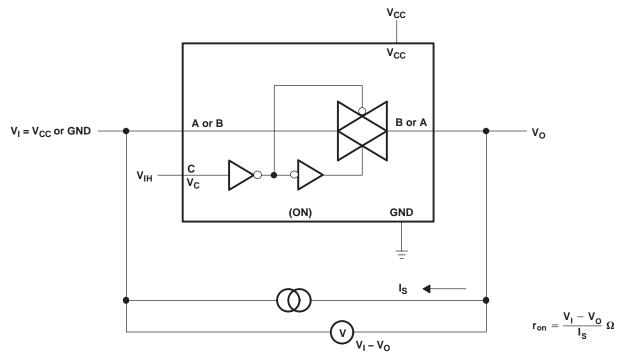


Figure 1. On-State Resistance Test Circuit

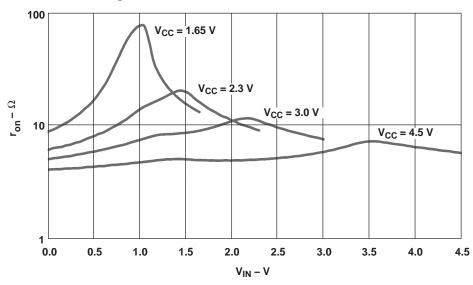


Figure 2. Typical r_{on} as a Function of Input Voltage (V_I) for $V_{I} = 0$ to V_{CC}



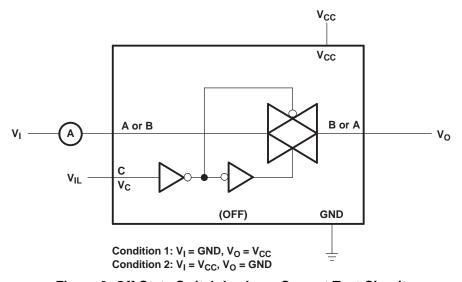


Figure 3. Off-State Switch Leakage-Current Test Circuit

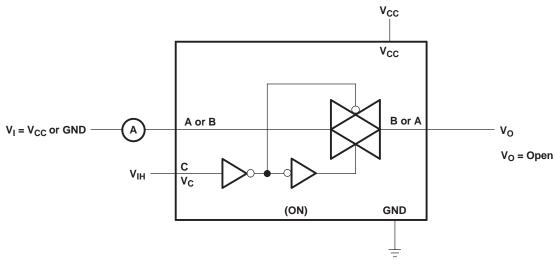
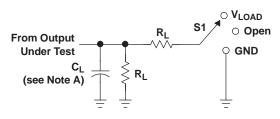


Figure 4. On-State Switch Leakage-Current Test Circuit

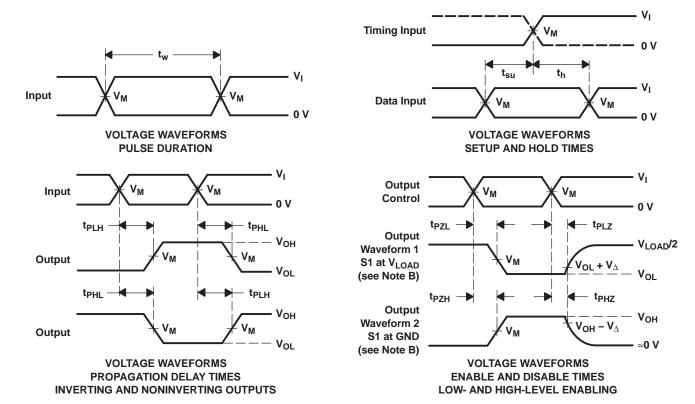




TEST	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INF	PUTS	.,	.,			.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	$oldsymbol{V}_\Delta$
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V_{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	V_{CC}	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	v_{cc}	≤2.5 ns	V _{CC} /2	2×V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
- F. t_{PZL} and t_{PZH} are the same as t_{en}.
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms



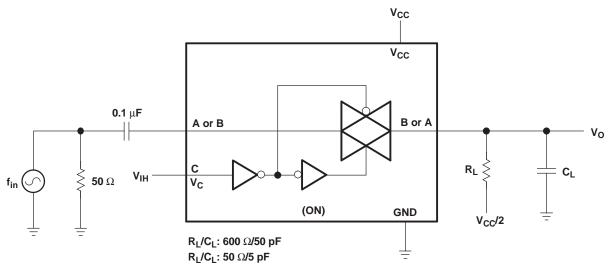


Figure 6. Frequency Response (Switch ON)

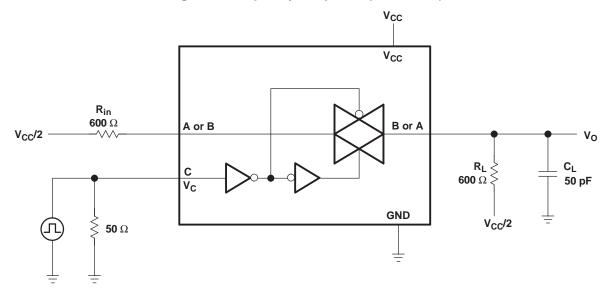


Figure 7. Crosstalk (Control Input – Switch Output)



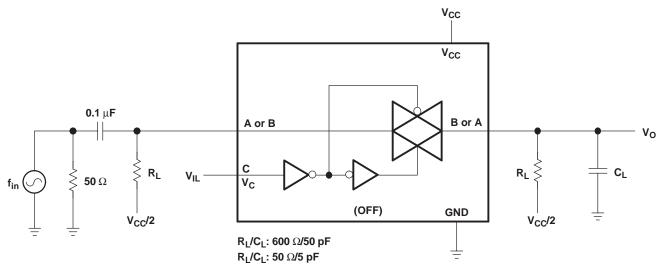


Figure 8. Feedthrough (Switch OFF)

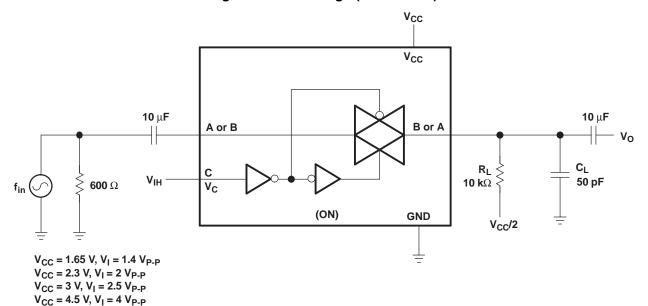


Figure 9. Sine-Wave Distortion

SCES323M – JUNE 2001 – REVISED JANUARY 2012



REVISION HISTORY

Cł	hanges from Revision L (January 2007) to Revision M	Page
•	Added DSF and DRY packge to pin out graphic.	1
•	Added Added DSF and DRY package to the ORDERING INFORMATION table.	2

1-Jun-2012

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
SN74LVC1G66DBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DBVRE4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DBVTE4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKRE4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKT	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKTE4	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DCKTG4	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DRLR	ACTIVE	SOT	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DRLRG4	ACTIVE	SOT	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DRYR	ACTIVE	SON	DRY	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66DSFR	ACTIVE	SON	DSF	6	5000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
SN74LVC1G66YZPR	ACTIVE	DSBGA	YZP	5	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	



PACKAGE OPTION ADDENDUM

1-.lun-2012

(1) The marketing status values are defined as follows:

www.ti.com

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF SN74LVC1G66:

Automotive: SN74LVC1G66-Q1

NOTE: Qualified Version Definitions:

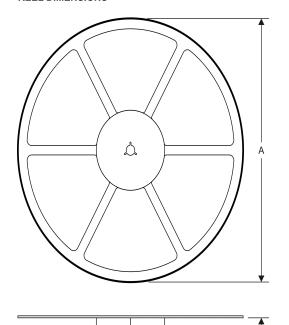
Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

PACKAGE MATERIALS INFORMATION

www.ti.com 29-Jun-2012

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

All differsions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.2	1.55	4.0	8.0	Q3
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G66DBVT	SOT-23	DBV	5	250	178.0	9.2	3.3	3.2	1.55	4.0	8.0	Q3
SN74LVC1G66DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G66DCKR	SC70	DCK	5	3000	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
SN74LVC1G66DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G66DRLR	SOT	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3
SN74LVC1G66DRLR	SOT	DRL	5	4000	180.0	9.5	1.78	1.78	0.69	4.0	8.0	Q3
SN74LVC1G66DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G66DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	180.0	8.4	1.02	1.52	0.63	4.0	8.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G66DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LVC1G66DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G66DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G66DCKR	SC70	DCK	5	3000	205.0	200.0	33.0
SN74LVC1G66DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G66DRLR	SOT	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G66DRLR	SOT	DRL	5	4000	180.0	180.0	30.0
SN74LVC1G66DRYR	SON	DRY	6	5000	180.0	180.0	30.0
SN74LVC1G66DSFR	SON	DSF	6	5000	180.0	180.0	30.0
SN74LVC1G66YZPR	DSBGA	YZP	5	3000	220.0	220.0	34.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-178 Variation AA.



DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.



DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



DRL (R-PDSO-N5)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs.

 Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
- D. JEDEC package registration is pending.



DRL (R-PDSO-N5)

PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
- E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Side aperture dimensions over—print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.





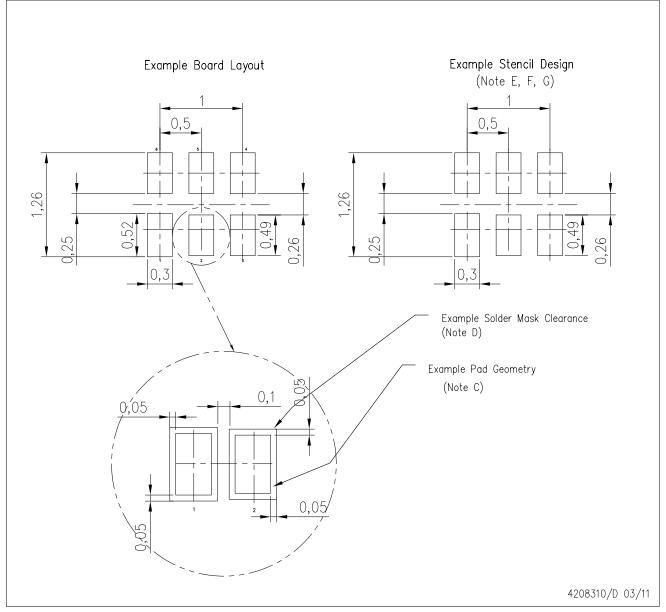
NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. SON (Small Outline No-Lead) package configuration.
- The exposed lead frame feature on side of package may or may not be present due to alternative lead frame designs.
- E. This package complies to JEDEC MO-287 variation UFAD.
- $frac{f}{K}$ See the additional figure in the Product Data Sheet for details regarding the pin 1 identifier shape.



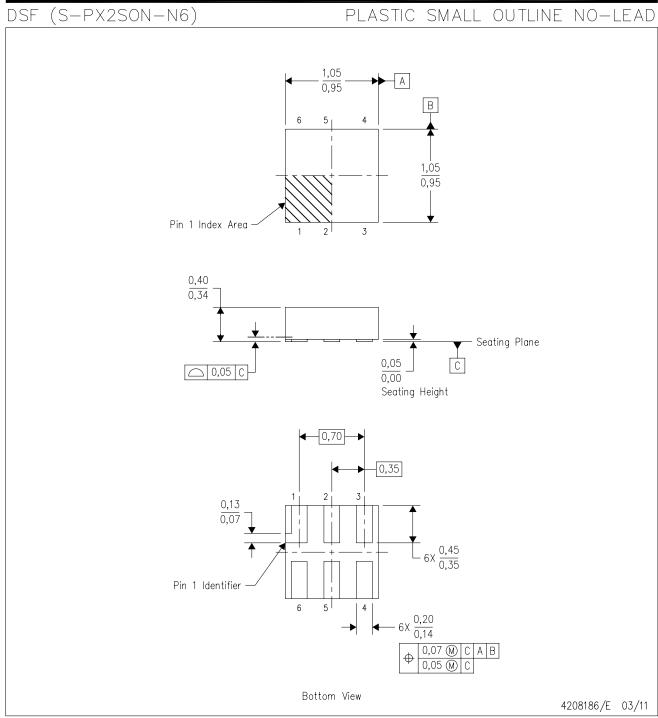
DRY (S-PUSON-N6)

PLASTIC SMALL OUTLINE NO-LEAD



- NOTES: A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.
 - E. Maximum stencil thickness 0,127 mm (5 mils). All linear dimensions are in millimeters.
 - F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - G. Side aperture dimensions over-print land for acceptable area ratio > 0.66. Customer may reduce side aperture dimensions if stencil manufacturing process allows for sufficient release at smaller opening.





NOTES: All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
 C. SON (Small Outline No-Lead) package configuration.
 D. This package complies to JEDEC MO-287 variation X2AAF.





PLASTIC SMALL OUTLINE NO-LEAD



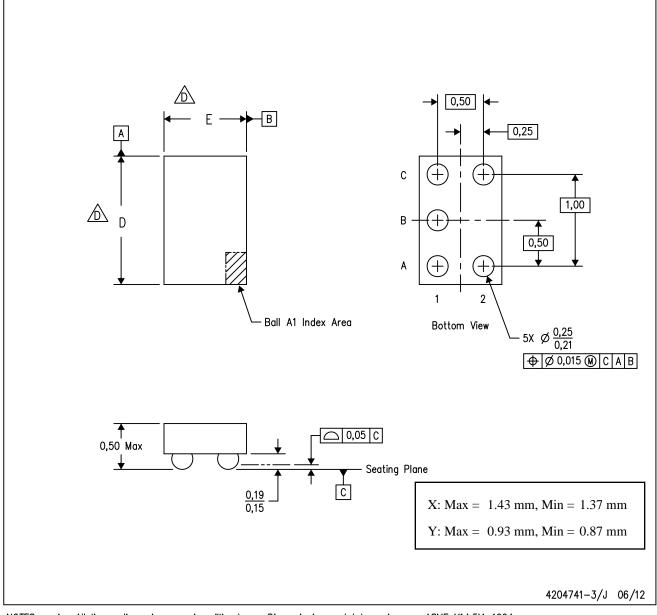
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads. If 2 mil solder mask is outside PCB vendor capability, it is advised to omit solder mask.
- E. Maximum stencil thickness 0,1016 mm (4 mils). All linear dimensions are in millimeters.
- F. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- G. Suggest stencils cut with lasers such as Fiber Laser that produce the greatest positional accuracy.
- H. Component placement force should be minimized to prevent excessive paste block deformation.



YZP (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- The package size (Dimension D and E) of a particular device is specified in the device Product Data Sheet version of this drawing, in case it cannot be found in the product data sheet please contact a local TI representative.
- E. This package is a Pb-free solder ball design. Refer to the 5 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



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